

Abstract

A system for an apparatus of the type adapted to treat substrates and/or wafers is described and comprises a stationary base element and a movable support for at least one substrate or at least one wafer, the support being rotatable above the element about a stationary axis; a chamber, and at least one duct is provided for the admission of at least one gas-flow to the chamber in order to raise the support; the system also comprises means for converting the flow of gas into the chamber into rotation of the support.

Exr Amde

dm

8/6/2007